

#### **Features**

- High isolation 5000 VRMS
- Patented coplanar structure DMC-Isolator®
- Various CTR selection available
- DC input with Transistor output
- Operating Temperature range 55 °C to 110 °C
- External creepage distance ≥ 7.0mm
- Distance Through Isolation ≥ 0.4mm
- Clearances Distance ≥ 7.5mm (S/SL Type)
- Clearances Distance ≥ 8.0mm (M/SLM Type)
- RoHS and REACH compliance
- Halogen Free compliance (Optional)
- MSL class 1
- Regulatory Approvals
  - ✓ UL UL1577 (E364000)
  - ✓ VDE EN60747-5-5(VDE0884-5)
  - ✓ CQC GB4943.1, GB8898 (14001104781)
  - ✓ IEC62368 (FI/41119)

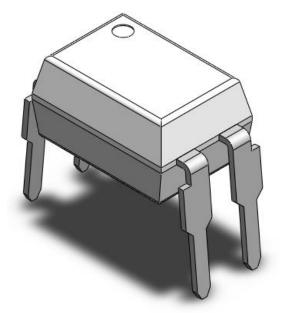
#### **Description**

The CT816 series consists of a photo transistor optically coupled to an Infrared-emitting diode in a 4-lead DIP DMC-Isolator® package with different lead forming options.

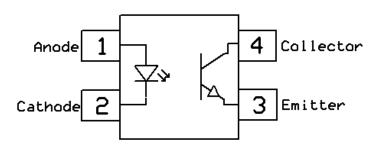
### **Applications**

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

### **Package Outline**



### **Schematic**



Note: Different bending options available. See package dimension



### Absolute Maximum Ratings $T_A = 25^{\circ}C$ , unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V <sub>RMS</sub>	
Topr	Operating temperature	-55 ~ +110	°C	
Tstg	Storage temperature	-55 ~ +150	°C	
Tsol	Soldering temperature (For 10 seconds)	260	°C	
Ртот	Total power dissipation	200	mW	
Emitter		•	<u> </u>	
I <sub>F</sub>	Forward current	60	mA	
I <sub>F</sub> (TRANS)	Peak transient current (≤1µs P.W,300pps)	1	А	
VR	Reverse voltage	6	V	
P <sub>D</sub>	Emitter power dissipation	100	mW	
Detector		•	<u> </u>	
Pc	Power dissipation	150	mW	
B <sub>VCEO</sub>	Collector-Emitter Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	6	V	
Ic	Collector Current	50	mA	



### **Electrical Characteristics** $T_A = 25$ °C, unless otherwise specified

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I <sub>F</sub> =10mA	-	1.24	1.4	V	
I <sub>R</sub>	Reverse Current	V <sub>R</sub> = 6V	-	-	5	μΑ	
Cin	Input Capacitance	f= 1MHz	-	30	-	pF	

#### **Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
B <sub>VCEO</sub>	Collector-Emitter Breakdown	Ic= 100μA	80	-	-	V	
Bveco	Emitter-Collector Breakdown	I <sub>E</sub> = 100μA	6	-	-	V	
ICEO	Collector-Emitter Dark Current	V <sub>CE</sub> = 20V, I <sub>F</sub> =0mA			100	nA	



### Electrical Characteristics $\tau_A = 25$ °C, unless otherwise specified

#### **Transfer Characteristics**

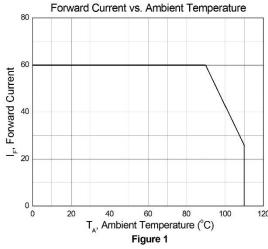
Symbol	Parameters	;	Test Conditions	Min	Тур	Max	Units	Notes
	CT816 CT816A		50	-	600			
		CT816A	_	80	-	160	%	
		CT816B		130	-	260		
CTR	Current Transfer Ratio	CT816C	I <sub>F</sub> = 5mA, V <sub>CE</sub> = 5V	200	-	400		
		CT816D		300	-	600		
		CT816F		100	-	200		
		CT816Y		200		300		
	Current Transfer Ratio	CT816I	- I <sub>F</sub> = 10mA, V <sub>CE</sub> = 5V	63	-	125	%	
		CT816J		100	-	200		
		CT816K		160	-	320		
CTR		CT816N		40		80		
CIK		CT816I		22	-	-		
		CT816J	I <sub>F</sub> = 1mA, V <sub>CE</sub> = 5V	34	-	-		
		CT816K		56	-	-		
		CT816N		13				
V	Collector-Emitter Saturation		I <sub>F</sub> = 20mA, I <sub>C</sub> = 1mA		0.1	0.2	V	
VCE(SAT)	Voltage			-	0.1	0.2	V	
R <sub>IO</sub>	Isolation Resistance		V <sub>IO</sub> = 500V <sub>DC</sub> , 40 ~ 60% R.H.	5x10 <sup>10</sup>	-	-	Ω	
Cio	Isolation Capacitance		f= 1MHz	-	0.25	1	pF	

### **Switching Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
tr	Rise Time	I <sub>C</sub> = 2mA, V <sub>CE</sub> = 2V, R <sub>L</sub> = 100Ω		6	18	0	
t <sub>f</sub>	Fall Time	IC= ZIIIA, VCE= ZV, KL= 100s2		8	18	μS	



### Typical Characteristic Curves $T_A = 25$ °C, unless otherwise specified



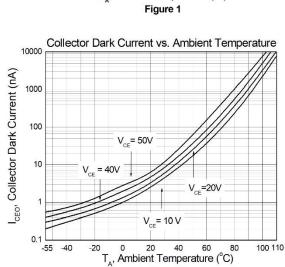
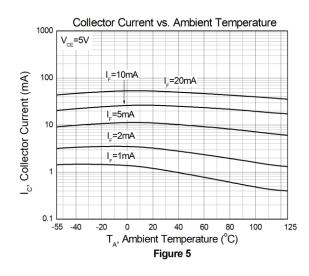
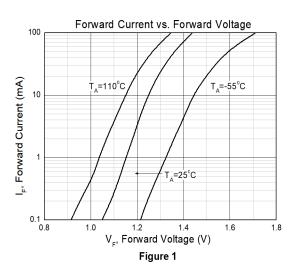
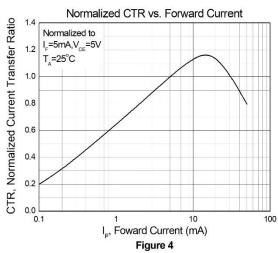
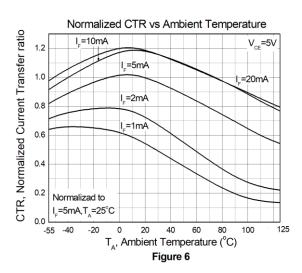


Figure 3



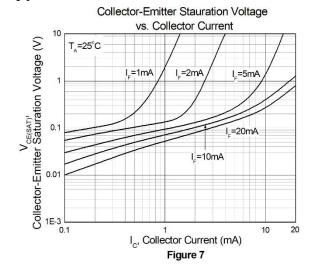


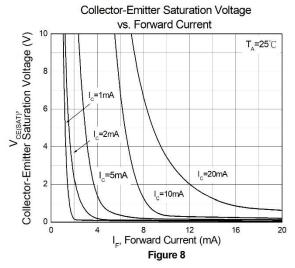


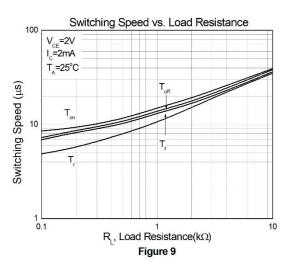


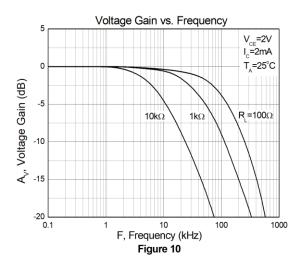


### Typical Characteristic Curves $T_A = 25$ °C, unless otherwise specified (Continued)



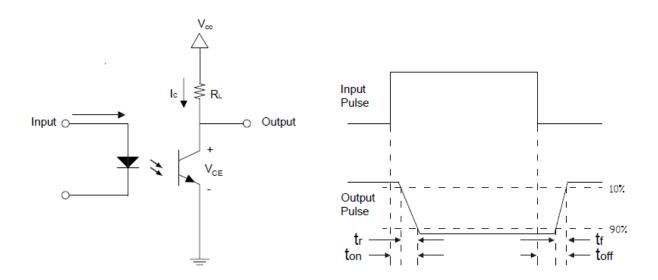








### **Test Circuit**

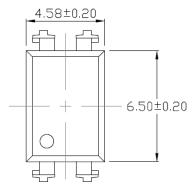


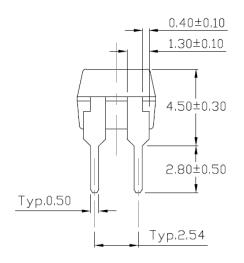
**Figure 11: Switching Time Test Circuits** 

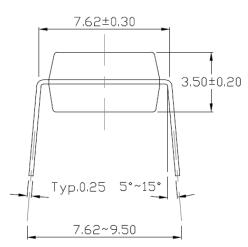


### Package Dimension Dimensions in mm unless otherwise stated

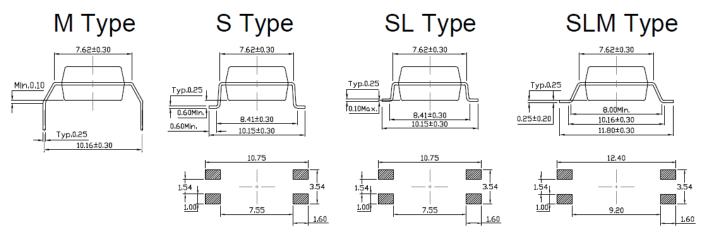
### Standard DIP - Through Hole





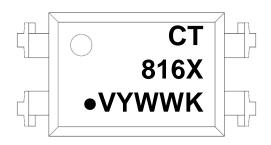


### **Forming Option**





#### **Marking Information**



Note:

CT : Denotes "CT Micro"

816 : Part Number

X : CTR Rank Option (Blank, A, B, C or D)V : VDE Safety Mark Option (Blank or V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code

: Lead Frame Material Option

(Blank: Iron; •: Copper)

### **Ordering Information**

### CT816X (V)(Y)(Z)-HG

CT = Denotes "CT Micro"

816 = Part Number

X = CTR Rank Option (Blank, A, B, C, D, I, J, K, N, F or Y)

V = VDE Safety Mark Option (Blank or V)

Y = Lead Form Option (S, SL, M, SLM or Blank)

Z = Tape and Reel Option (Blank, T1 or T2)

H = Lead Frame Option (H: Iron, Blank: Copper)

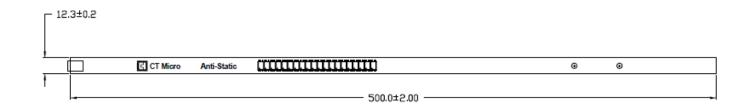
G = Material Option (G: Halogen Free, Blank: Non-Halogen Free)

Option	Description	Quantity
None	Standard 4 Pin DIP	100 Units/Tube
M	Gullwing (400mil) Lead Forming	100 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1500 Units/Reel
S(T2)	S(T2) Surface Mount Lead Forming – With Option 2 Taping	
SL(T1)	SL(T1) Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	
SL(T2)	SL(T2) Surface Mount (Low Profile) Lead Forming – With Option 2 Taping	
SLM(T1)	SLM(T1) Surface Mount (Gullwing) Lead Forming– With Option 1 Taping	
SLM(T2)	Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	1500 Units/Reel

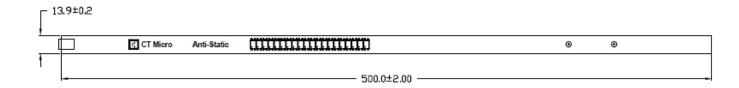


### Carrier Specifications Dimensions in mm unless otherwise stated

#### **Tube Option Standard DIP**



### **Tube Option M Type**

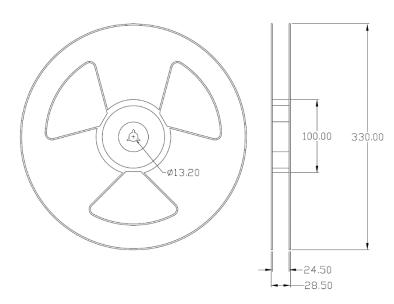


### Reel Dimension All dimensions are in mm, unless otherwise stated

### **Option S(T1/T2) & SL(T1/T2)**

# 100.00 330.00 \$\phi\_{13.20}\$ -16.50 -20.50

### Option SLM(T1/T2)

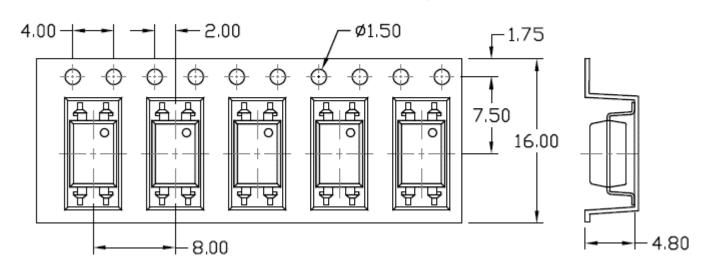




### Carrier Tape Specifications Dimensions in mm unless otherwise stated

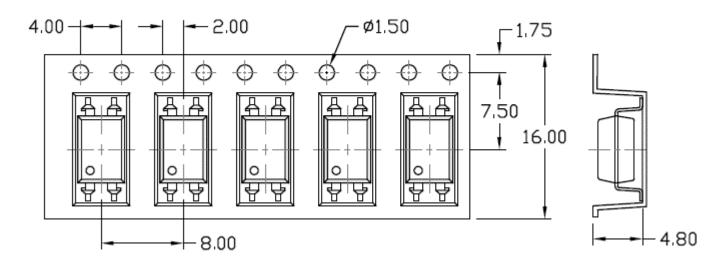
Option S(T1) & SL(T1)

### Input Direction



### Option S(T2) & SL(T2)

### Input Direction

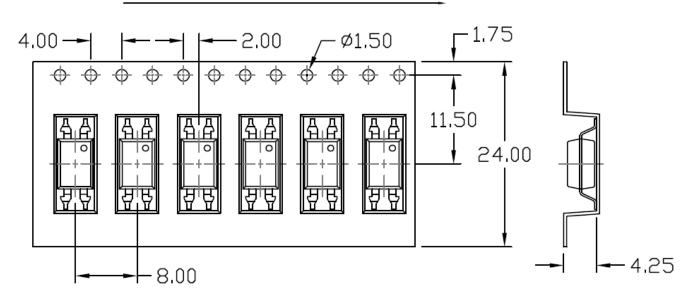






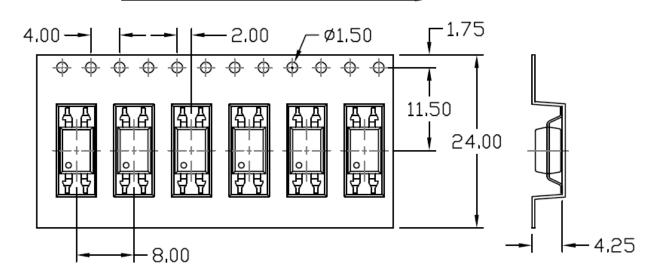
#### Option SLM(T1)

### Input Direction



#### **Option SLM(T2)**

### Input Direction



**Phototransistor Optocoupler** 



### Solderability spec (Follow the JEDEC standard JESD22-B102)

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

### **Wave soldering (Follow the JEDEC standard JESD22-A111)**

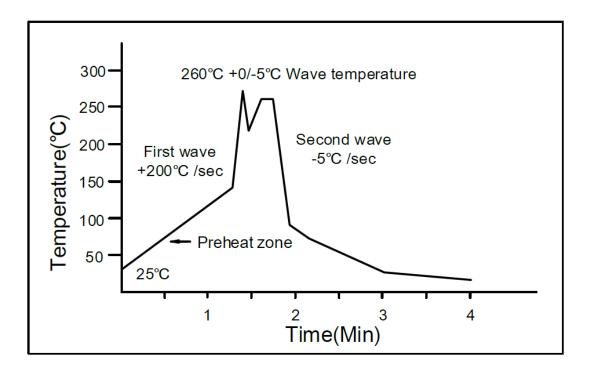
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature: 25 to 140°C.

Preheat time: 30 to 80 sec.



### Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

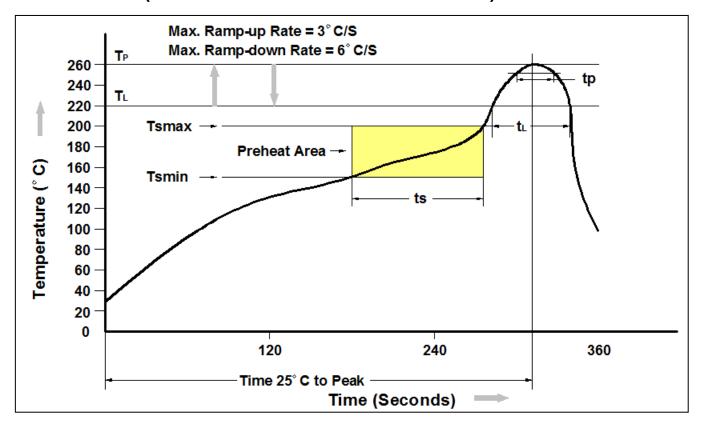
Allow single lead soldering in every single process.

One time soldering is recommended. Temperature: 350±10°C

Time: 5 sec max.



### Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t₂)	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



#### **DISCLAIMER**

DMC-Isolator® IS A TRADEMARK OF CT MICRO INTERNATIONAL CORPORATION AND/OR ITS SUBSIDIARIES. CT MICRO OWNS THE RIGHTS TO A NUMBER OF PATENTS, TRADEMARKS, COPYRIGHTS AND OTHER INTELLECTUAL PROPERTY.

CT MICRO RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS
HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. CT MICRO DOES NOT ASSUME ANY LIABILITY
ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN;

NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

DISCOLORATION MIGHT OCCUR ON THE PACKAGE SURFACE AFTER SOLDERING, REFLOW OR LONG TERM USE. THIS DOES NOT IMPACT THE PRODUCT PERFORMANCE NOR THE PRODUCT RELIABILITY.

CT MICRO ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT EXPRESS WRITTEN APPROVAL OF CT MICRO INTERNATIONAL CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### 单击下面可查看定价,库存,交付和生命周期等信息

### >>CT-MICRO(兆龙科技)